

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11363	((427,526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)). COLS.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/22 18:54
L2	6828	(SOI GeSiOI GSIO GeSiOI GESiOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L3	4777	(Vacancies voids pores porous porosity damag\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dope\$2)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L4	70	L2 same L3	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L5	247	L2 and L3	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L6	70	L4 and L5	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L7	177	L5 not L6	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54

L8	2232	"HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofluoride Hydrofluoricaad hydrofluorideacid Hydro adj (fluoride fluoric florica) Same (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L9	54	L7 and L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L10	1	L9 and L1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L11	53	L9 not L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L12	123	L7 not (L6 or L10 or L11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L13	31	L6 and L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L14	123	L7 not (L6 or L10 or L11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L15	53	L14 and (Vacancies voids pores porous porosity ) with (percent percentages "%" grade\$2 grading different differential\$3 differential\$4 vary\$4 varied)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54

L16	247	(L6 or L10 or L11 or L12 or L13 or L15)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:54
L17	19	L16 and @pd> "20080619"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 18:57
L18	3617	(SOI GeSOI GSOI GeSOI GESOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7) with ((Si silicon Ge germanium Ne neon Bi bismuth Sn "tin./c."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 19:15
L19	643	(SOI GeSOI GSOI GeSOI GESOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7) with ((Si silicon) near ion "Si.sup.+" Ge germanium Ne neon Bi bismuth Sn "tin./c."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 19:18
L20	28	L3 and L2 and L19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 19:19
L21	0	L20 not L16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/22 19:20

3/22/2009 7:21:01 PM

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